# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

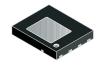
Texas Instruments
CSD16325Q5C

For any questions, you can email us directly: <a href="mailto:sales@integrated-circuit.com">sales@integrated-circuit.com</a>

Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com





CSD16325Q5C

www.ti.com

SLPS237B - DECEMBER 2009-REVISED APRIL 2010

## **DualCool™ N-Channel NexFET™ Power MOSFETs**

Check for Samples: CSD16325Q5C

#### **FEATURES**

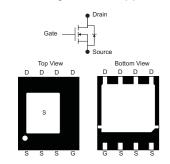
- DualCool™ Package SON 5×6mm
- Optimized for 2-Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Avalanche Rated
- · Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

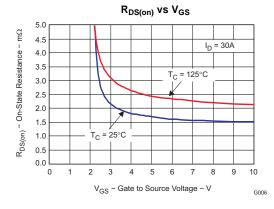
#### **APPLICATIONS**

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

#### **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.





#### **PRODUCT SUMMARY**

$V_{DS}$	Drain to Source Voltage	25	V	
$Q_g$	Gate Charge Total (4.5V)	ate Charge Total (4.5V) 18		
$Q_{gd}$	Gate Charge Gate to Drain	3.5	nC	
		$V_{GS} = 3V$	2.1	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V$	1.7	mΩ
		V <sub>GS</sub> = 8V 1.5		mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V	

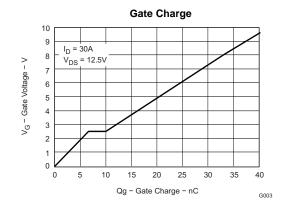
#### **ORDERING INFORMATION**

Device	evice Package Media		Qty	Ship	
CSD16325Q5C	SON 5×6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel	

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	+10 / -8	V
ı	Continuous Drain Current, T <sub>C</sub> = 25°C	100	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>		Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	200	Α
$P_D$	Power Dissipation <sup>(1)</sup>	3.1	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D$ = 100A, L = 0.1mH, $R_G$ = 25 $\Omega$	500	mJ

- (1) Typical  $R_{\theta JA}=38^{\circ}\text{C/W}$  on 1-in  $^2$  Cu, (2-oz.) on a 0.060" thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DualCool, NexFET are trademarks of Texas Instruments.



Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

### CSD16325Q5C



SLPS237B - DECEMBER 2009-REVISED APRIL 2010

www.ti.com



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Cl	haracteristics				
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25		V
I <sub>DSS</sub>	Drain to Source Leakage	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V		1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V, I_{D} = 30A$	2.1	2.9	$m\Omega$
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 30A$	1.7	2.2	mΩ
		$V_{GS} = 8V, I_{D} = 30A$	1.5	2	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_D = 30A$	159		S
Dynamic	c Characteristics	,		•	
C <sub>iss</sub>	Input Capacitance		3070	4000	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$	2190	2850	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 10012	120	150	рF
$R_{G}$	Series Gate Resistance		1.6	3.2	Ω
Qg	Gate Charge Total (4.5V)		18	25	nC
Q <sub>gd</sub>	Gate Charge – Gate to Drain	V <sub>DS</sub> = 12.5V,	3.5		nC
Q <sub>gs</sub>	Gate Charge – Gate to Source	I <sub>DS</sub> = 30A	6.6		nC
Q <sub>g(th)</sub>	Gate Charge at Vth		3.1		nC
Q <sub>oss</sub>	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	43		nC
t <sub>d(on)</sub>	Turn On Delay Time		10.5		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$	16		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 30A$ , $R_G = 2\Omega$	32		ns
t <sub>f</sub>	Fall Time		12		ns
Diode C	haracteristics			·	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>DS</sub> = 30A, V <sub>GS</sub> = 0V	0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V = 13V I = 30A di/dt = 300A/::2	63		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 30A$ , $di/dt = 300A/\mu s$	47		ns

### THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) <sup>(1)</sup>			1.4	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom drain) <sup>(1)</sup>			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			50	°C/W

 <sup>(1)</sup> R<sub>θJC</sub> is determined with the device mounted on a 1-inch² 2-oz. Cu pad on a 1.5 x 1.5-inch 0.060-inch thick FR4 board. R<sub>θJC</sub> is specified by design, whereas R<sub>θCA</sub> is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² of 2-oz. Cu.

Product Folder Link(s): CSD16325Q5C

Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

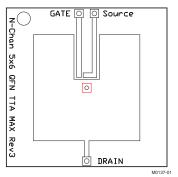
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



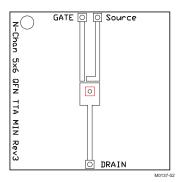
CSD16325Q5C

#### www.ti.com

SLPS237B - DECEMBER 2009-REVISED APRIL 2010



Max  $R_{\theta JA} = 50^{\circ}$ C/W when mounted on 1 inch<sup>2</sup> of 2-oz. Cu.



Max  $R_{0JA} = 126^{\circ}$ C/W when mounted on minimum pad area of 2-oz.Cu.

### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

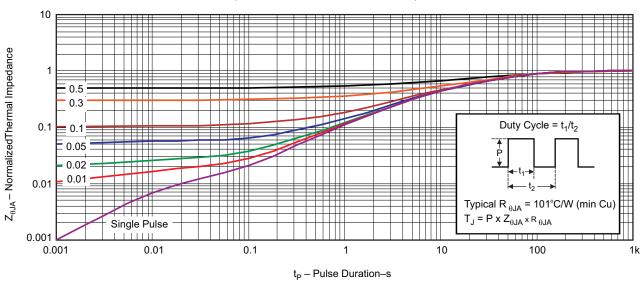


Figure 1. Transient Thermal Impedance

G012

### CSD16325Q5C



SLPS237B - DECEMBER 2009-REVISED APRIL 2010

www.ti.com

## **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

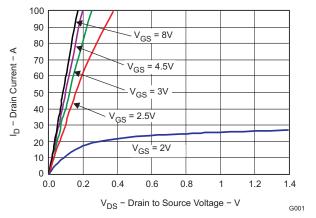


Figure 2. Saturation Characteristics

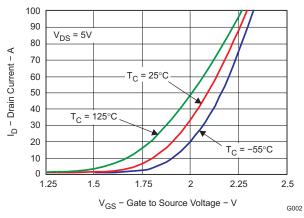


Figure 3. Transfer Characteristics

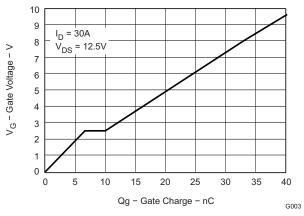


Figure 4. Gate Charge

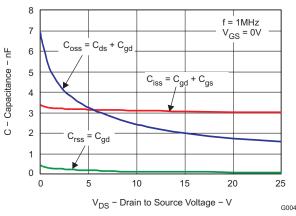


Figure 5. Capacitance

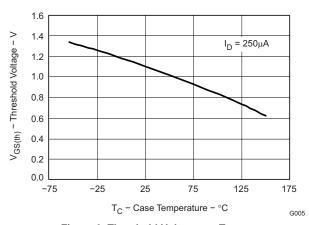


Figure 6. Threshold Voltage vs. Temperature

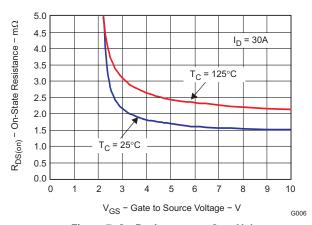


Figure 7. On Resistance vs. Gate Voltage

www.ti.com



CSD16325Q5C

SLPS237B – DECEMBER 2009 – REVISED APRIL 2010

### **TYPICAL MOSFET CHARACTERISTICS (continued)**

#### $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

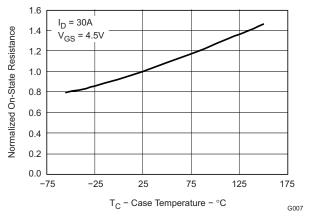


Figure 8. On Resistance vs. Temperature

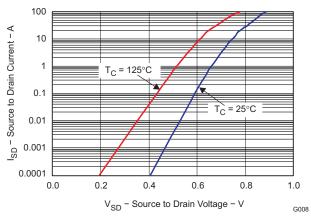


Figure 9. Typical Diode Forward Voltage

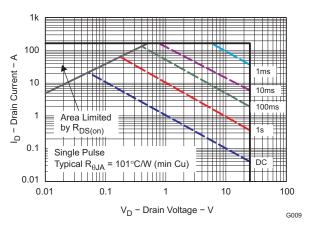


Figure 10. Maximum Safe Operating Area

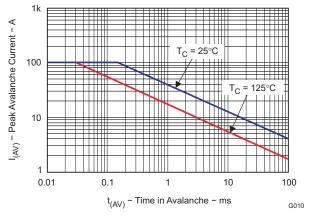


Figure 11. Single Pulse Unclamped Inductive Switching

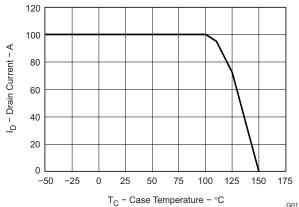


Figure 12. Maximum Drain Current vs. Temperature

Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

## CSD16325Q5C

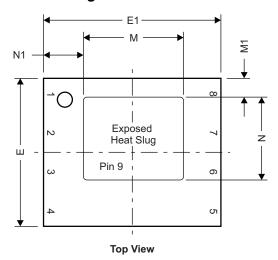


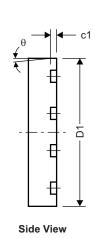
SLPS237B - DECEMBER 2009-REVISED APRIL 2010

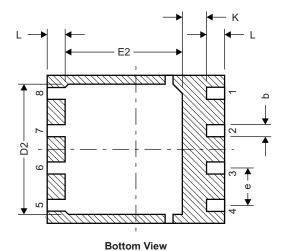
www.ti.com

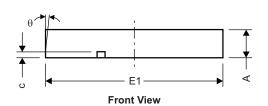
### **MECHANICAL DATA**

### **Q5C Package Dimensions**









DualCool™Pinout					
Pin# Label					
1, 2, 3, 9	Source				
4	Gate				
5, 6, 7, 8	Drain				

M0162-01

DIM	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
А	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	D2 4.320		0.170	0.178	
Е	E 4.900		0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	' TYP	0.050		
L	0.510	0.710	0.020	0.028	
θ	_	_	_	_	
K	0.760	_	0.030	_	
M	3.260	3.460	0.128	0.136	
M1	0.520	0.720	0.020	0.028	
N	2.720	2.920	0.107	0.115	
N1	1.227	1.427 0.048		0.056	

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



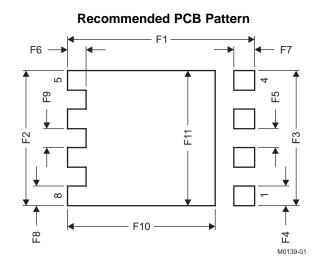
Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON



CSD16325Q5C

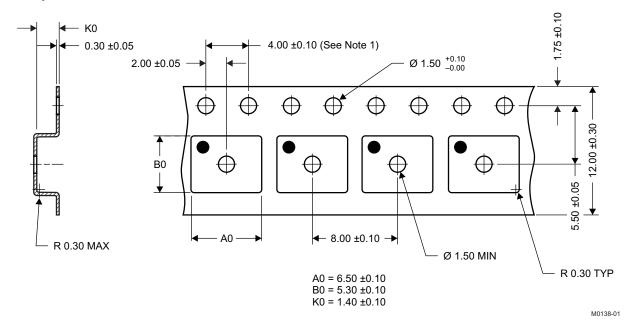
www.ti.com

SLPS237B - DECEMBER 2009-REVISED APRIL 2010



DIM	MILLIM	ETERS	INCHES			
DIN	MIN	MAX	MIN	MAX		
F1	6.205	6.305	0.244	0.248		
F2	4.46	4.56	0.176	0.18		
F3	4.46	4.56	0.176	0.18		
F4	0.65	0.7	0.026	0.028		
F5	0.62	0.67	0.024	0.026		
F6	0.63	0.68	0.025	0.027		
F7	0.7	0.8	0.028	0.031		
F8	0.65	0.7	0.026	0.028		
F9	0.62	0.67	0.024	0.026		
F10	4.9	5	0.193	0.197		
F11	4.46	4.56	0.176	0.18		

### **Q5C Tape and Reel Information**



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

## CSD16325Q5C



SLPS237B - DECEMBER 2009-REVISED APRIL 2010

www.ti.com

#### **REVISION HISTORY**

Changes from Original (December 2009) to Revision A					
Changed the labels on the Bottom View pinout image	1				
Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1	6				
Changes from Revision A (April 2010) to Revision B	Page				
• Changed $R_{DS(on)}$ - $V_{GS}$ = 3V in the Electrical Characteristics table From: 2.7 To: 2.9 in the max column	2				
Deleted the Package Marking Information section	7				

Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

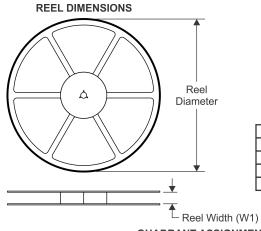
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

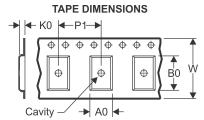


## **PACKAGE MATERIALS INFORMATION**

www.ti.com 15-Apr-2014

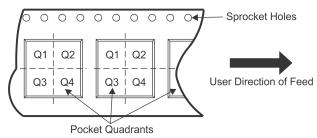
### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16325Q5C	VSON- CLIP	DQU	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1



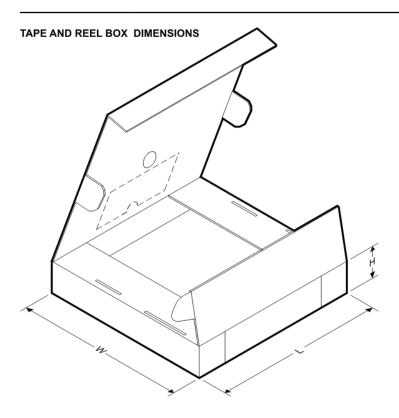
Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



## **PACKAGE MATERIALS INFORMATION**

www.ti.com 15-Apr-2014



### \*All dimensions are nominal

Device	Package Type	ge Type Package Drawing		SPQ	Length (mm) Width (mm)		Height (mm)	
CSD16325Q5C	VSON-CLIP	DQU	8	2500	335.0	335.0	32.0	



Datasheet of CSD16325Q5C - MOSFET N-CH 25V 100A 8SON

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Amplifiers amplifier.ti.com Communications and Telecom www.ti.com/communications Computers and Peripherals www.ti.com/computers **Data Converters** dataconverter.ti.com **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps DSP dsp.ti.com **Energy and Lighting** www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical

Interface Interface.ti.com Medical www.ti.com/medical Logic Security www.ti.com/security

Power Mgmt Space, Avionics and Defense <u>www.ti.com/space-avionics-defense</u>

Microcontrollers <u>microcontroller.ti.com</u> Video and Imaging <u>www.ti.com/video</u>

RFID <u>www.ti-rfid.com</u>

OMAP Applications Processors <a href="https://www.ti.com/omap">www.ti.com/omap</a> TI E2E Community <a href="https://e2e.ti.com">e2e.ti.com</a>

Wireless Connectivity www.ti.com/wirelessconnectivity

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2014, Texas Instruments Incorporated